



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-16 A

Features

- $R_{DS(ON)}$, V_{GS} @-10V, I_D @-8A<48 $m\Omega$
- $R_{DS(ON)}$, V_{GS} @-4.5V, I_{D} @-4A<65 $m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

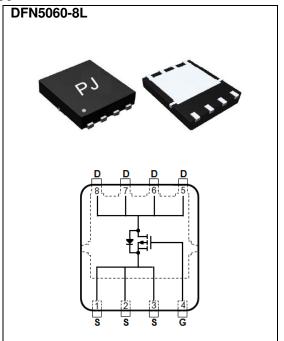
Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams

Marking: Q5465A



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	٧	
Continuous Drain Current	T _C =25°C	l _D	-16	А	
	T _C =100°C		-10		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-64		
Power Dissipation	T _C =25°C	Po	25	14/	
	T _C =100°C		10	W	
Continuous Drain Current	T _A =25°C	I _D	-5.0	Α	
	T _A =70°C		-4.0	Α	
Power Dissipation	T _A =25°C	1	2.0	W	
Power Dissipation	T _A =70°C	Po	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	51	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	5.0	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V,I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-1.0	-1.7	-2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V,I _D =-8A	-	40	48	mΩ
		V _{GS} =-4.5V,I _D =-4A	-	55	65	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-60V, V_{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V_{DS} =-30V, I_{D} =-8A, V_{GS} =-10V (Note 3)	-	22	-	nC
Gate-Source Charge	Q_gs		-	4.1	-	
Gate-Drain Charge	Q_gd		-	5.2	-	
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V, f=1.0MH <i>Z</i>	-	1256	-	pF
Output Capacitance	Coss		-	87	-	
Reverse Transfer Capacitance	Crss	I=I.UIVIMZ	-	59	-	
Turn-On Delay Time	td _(on)	\/ 00\/ 4A	-	13	-	
Turn-On Rise Time	t _r	V_{DD} =-30V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 3)	-	42	-	ns
Turn-Off Delay Time	td _(off)		-	65	-	
Turn-Off Fall Time	t _f		-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					-16	^
Diode Forward Current	I _S		-	-	-10	Α
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	-0.72	-1.0	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =32A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

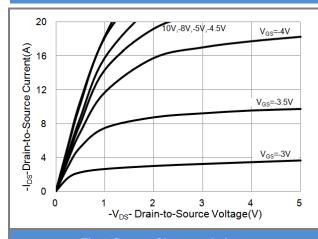


Fig.1 Output Characteristics

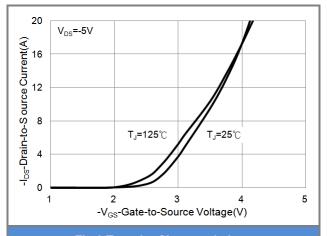


Fig.2 Transfer Characteristics

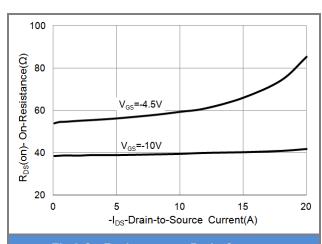


Fig.3 On-Resistance vs. Drain Current

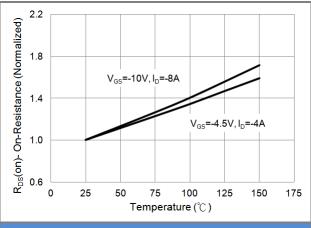


Fig.4 On-Resistance vs. Junction temperature

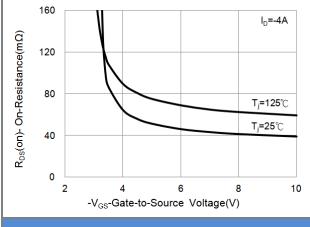


Fig.5 On-Resistance Variation with VGS.

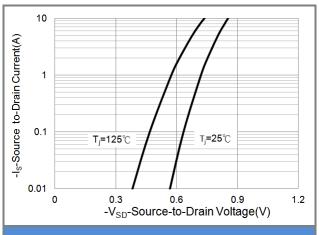


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

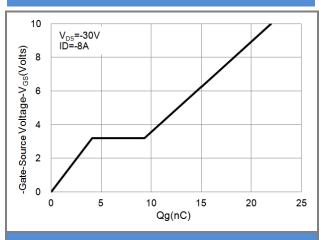


Fig.7 Gate-Charge Characteristics

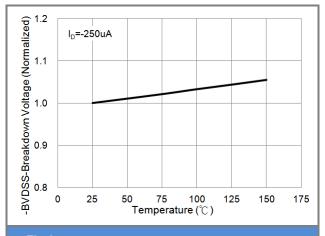


Fig.8 Breakdown Voltage Variation vs. Temperature

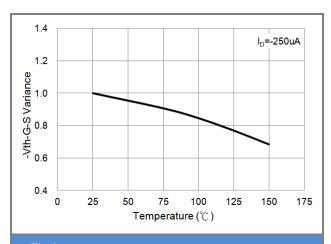


Fig.9 Threshold Voltage Variation with Temperature

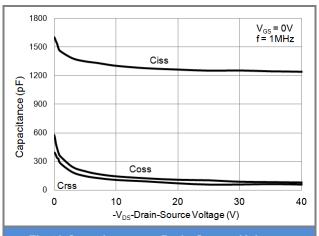
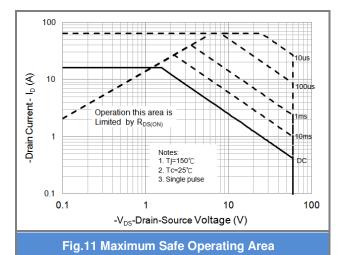


Fig.10 Capacitance vs. Drain-Source Voltage







TYPICAL CHARACTERISTIC CURVES

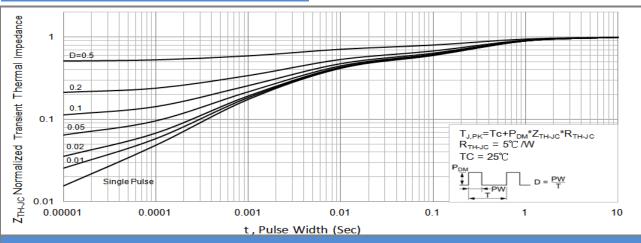


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

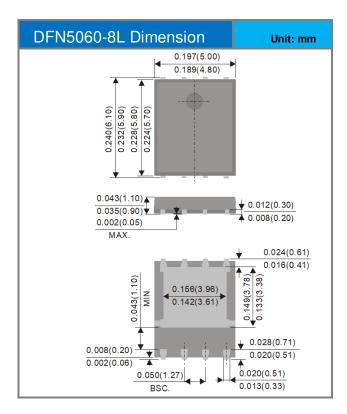


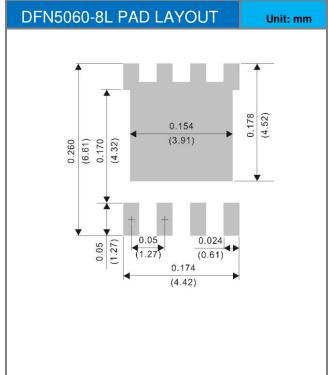


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type Marking		Version	
PJQ5465A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5465A	Halogen free	

Packaging Information & Mounting Pad Layout









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